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Femtosecond laser micromachining

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Femtosecond laser micromachining

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Nonlinear light-matter interaction, photoinduced material modifications

- Femtosecond laser optical waveguide writing
- Fabrication of integrated photonic devices
 - ➤ passive devices
 - ➤ active devices
- Femtosecond laser microstructuring for optofluidics
 - microfluidic channels by irradiation + etching
 - > new optofluidic functionalities by waveguide-channel integration

Femtosecond laser microstructuring for solar cells



Material modification following

nonlinear light absorption





 Simultaneous absorption of k photons brings electron from valence to conduction band

$$\frac{dn}{dt} = \sigma_k I^k(t)$$

n(t) electron density l(t) laser intensity σ_k k-photon absorption cross section



Avalanche ionization

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 Free electrons in the conduction band are accelerated by the laser field until they have enough kinetic energy to kick another electron into the conduction band

$$\frac{dn}{dt} = \alpha I(t)n(t)$$

 $\boldsymbol{\alpha}$ avalanche ionization coefficient



Femtosecond absorption

• The peak power is sufficient to trigger, in the focus, **multiphoton ionization** which provides a **seed of electrons** in the conduction band

• The electrons are accelerated by the laser and multiplied by avalanche ionization \Rightarrow deterministic and highly reproducible process

Long pulse absorption

• The peak power is too low for **multiphoton ionization**

• Avalanche ionization initiated by spurious free electrons in the conduction band from defects or impurities \Rightarrow **poorly reproducible** process



Femtosecond absorption

• The peak power is sufficient to trigger, in the focus, **multiphoton ionization** which provides a **seed of electrons** in the conduction band

• The electrons are accelerated by the laser and **multiplied by avalanche** ionization \Rightarrow deterministic and highly reproducible process



Femtosecond pulse absorption as a function of peak intensity (Rayner *et al.*, Opt. Express **13**, 3208 (2005))

Highly localized and reproducible deposition of energy in the focus of the laser beam

One photon vs multiphoton absorption



Light is absorbed only in the focus, where the intensity is sufficient

W. Denk et al., Science **248**, 73 (1990)



Timescales of light-matter interaction in transparent materials



Regimes of material modification





Femtosecond laser

optical waveguide writing

November 1, 1996 / Vol. 21, No. 21 / OPTICS LETTERS 1729

Writing waveguides in glass with a femtosecond laser

K. M. Davis, K. Miura, N. Sugimoto, and K. Hirao

Hirao Active Glass Project, Exploratory Research for Advanced Technology, Research Development Corporation of Japan, 15 Mori Moto-Cho, Shimogamo, Sakyo-Ku, Kyoto G06, Japan



(C) Formed Perpendicular to Laser Beam

Seminal paper by Hirao et al., demonstrating permanent positive refractive index changes

Not yet fully understood, several mechanisms have been proposed such as:

• Structural modifications, i.e. changes in the structure of the glass network

• **Color center formation**, with UV absorption causing a refractive index change through Kramers-Krönig

 Melting and rapid resolidification (quenching), causing regions of material densification

These mechanisms may act simultaneously.

A.M. Streltsov et al., J. Opt. Soc. Am. B **19**, 2496 (2002)



Advantages:

 Direct fabrication technique, no need for clean rooms and photolithography

Maskless technique, suitable for rapid prototyping

 Applicable to a wide variety of substrates, both amorphous and crystalline

3D device fabrication capabilities

Waveguide fabrication setup



• The basic setup is remarkably simple: laser, focusing optics, computercontrolled translation stage Amplified Ti:Sapphire systems: 100-200 fs long pulses at 800nm, few μJ energies per pulse, 1-200 kHz repetition rate

single-pulse regime

Diode-pumped fiber or bulk Yb lasers: 300-400 fs long pulses at 1040nm, < 1 μJ energies per pulse,200 kHz-2 MHz repetiton rate</p>

cumulative regime

Long-cavity Ti:Sapphire oscillators: 10-50 fs long pulses at 800nm, tens of nJ energy per pulse, 4-25 MHz repetition rate

Cumulative regime: pulse period much shorter than heat diffusion time out of the focal volume

repetition rate



• In transverse geometry, writing with low repetition rate systems provides waveguides with an intrinsically asymmetric cross section \rightarrow very poor coupling with standard fibers



The confocal parameter is much larger than the focal diameter

Solution: astigmatic beam shaping



Astigmatic beam shaping: experimental results



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S. Sowa et al., Opt. Expr. 14, 291 (2006)

Y. Nasu et al., Opt. Lett. 30, 723 (2005)



• Borosilicate glass. Heat diffusion time out of focal volume $\sim 1 \ \mu s$

S. Eaton et al., Opt. Express **16**, 9443 (2008)





Due to isotropic heat diffusion, waveguide cross section becomes symmetric

 Waveguide cross-section can be controlled by average power and translation speed

S. Eaton et al., Opt. Express **13**, 4708 (2005)

C. Schaffer et al., Appl. Phys. A **76**, 351 (2003)



Passive photonic devices

by femtosecond writing







• Single transverse mode waveguides with high circular symmetry at 1.5 μ m.

Mode matching with standard telecom fibers: 0.2 dB coupling losses (propagation losses < 0.2 dB/cm)</p>



Directional coupler



left input, cross coupling ratio 45.1 %

Bragg grating waveguide fabrication: single pulse method



Laser is scanned rapidly, so individual shots create periodic index modulation

G.D Marshall et al., Opt. Lett. **31**, 2690 (2006)

H. Zhang et al., Opt. Lett. **31**, 3495 (2006)





Writing beam intensity periodically modulated by acousto-optic modulator

H. Zhang *et al.*, Opt. Lett. **32**, 2559 (2007)





H. Zhang et al., Opt. Lett. 32, 2559 (2007)





Three-dimensional splitter written in fused silica

S. Nolte et al., Appl. Phys. A 77, 109 (2003)







A. M. Kowalevicz et al., Opt. Lett. 30, 1060 (2005)



Active photonic devices

by femtosecond writing







- Glass base suitable for compact active devices (high-gain per unit length)
- Allows for high doping concentration: 1-10 % weight Er₂O₃ or Yb₂O₃
- Three-level system, pumped at 980 nm and lasing at 1.5 μ m in the telecom band

Active waveguides with net gain in the whole telecom C-band



Internal gain (6 dB) overcomes insertion losses (1.4 dB) over the whole C band

Possibility of active devices such as waveguide amplifiers or lasers

R. Osellame et al., Opt. Lett. 29, 1902 (2004)

Femtosecond laser written Erbium-Doped Waveguide Amplifier





• Improved insertion losses (1.9 dB for L=37 mm \rightarrow propagation loss < 0.4 dB/cm)

Gain over the whole C-band: 7.4 dB peak at 1535 nm,3.7 dB at 1565 nm

G. Della Valle et al., Opt. Express **13**, 5976 (2005)

Femtosecond laser written waveguide laser



S. Taccheo et al., Opt. Lett. 29, 2626 (2004)
Single longitudinal mode waveguide laser







Femtosecond laser written Bragg gratings integrated into the waveguide

G.D. Marshall *et al.*, Opt. Lett. **33**, 956 (2008)



Femtosecond laser microfabrication for optofluidics applications



March 1, 2001 / Vol. 26, No. 5 / OPTICS LETTERS 277

Femtosecond laser-assisted three-dimensional microfabrication in silica

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Novel technique for the fabrication of directly buried microchannels in three dimensions

Femtosecond Laser Microchannel fabrication



Femtosecond irradiation



- High intensity femtosecond laser irradiation
- Selective etching in HF solution
- Fabrication of directly buried microchannels in three dimensions

Microchannel fabrication: underlying physical mechanism



- Nonlinear ionization creates randomly localized plasma nanodroplets
- The droplets grow and flatten under the electric field
- They merge to form regular arrays of nanoplanes

R. Taylor et al., Laser Photonics Reviews 2, 26 (2008)

Experimental evidence for the nanogratings



C. Hnatovsky et al., Opt. Lett. 30, 1867 (2005).

- Femtosecond laser irradiation followed by etching
- Grating planes are perpendicular to the direction of electric field
- Much higher etching rate when gratings are aligned along the writing direction





5.0kV

High aspect ratio surface channels

SEI



3 µm

3D directly buried channels

V. Maselli et al., Appl. Phys Lett. 88, 191107 (2006).

Y. Bellouard *et al.*, Opt. Express **12**, 2120 (2004).

X370

10µm

WD 21.0mm

10 µm

YB - RPI



Conical shape is intrinsic in the etching process of uniform structures



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• Conical shape is intrinsic in the etching process of uniform structures



K. Vishnubhatla et al., Opt. Express. 17, 8685 (2009).



Developing optofluidic technology through the fusion of microfluidics and optics

Demetri Psaltis¹, Stephen R. Quake² & Changhuei Yang¹

We describe devices in which optics and fluidics are used synergistically to synthesize novel functionalities. Fluidic replacement or modification leads to reconfigurable optical systems, whereas the implementation of optics through the microfluidic toolkit gives highly compact and integrated devices. We categorize optofluidics according to three broad categories of interactions: fluid-solid interfaces, purely fluidic interfaces and colloidal suspensions. We describe examples of optofluidic devices in each category.

Optofluidics

 Liquids may improve or extend the functionalities of integrated optical devices

 Integrated optics may enhance the sensing capabilities in fluidic devices



Femtosecond Micromachining for Optofluidics48



Direct femtosecond laser fabrication of integrated waveguides and microchannels

Use laser as post-processing tool adding new functionalities to microfluidic devices

Integration of femtosecond written waveguides and microchannels

- Single side: 1.8mm, Ø90µm
- Double side: 3mm, Ø100-50µm or 2.2mm, Ø110-90µm
- (a)
 (b)
 (c)
 100 μm
 - Waveguides provide selective excitation of a Rhodamine solution in the channel



Femtosecond laser written optofluidic cell detector



M. Kim et al., Lab on Chip 9, 311 (2009)

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A network of microfluidic channels allows to perform chemical processes or bio-analysis with very small amounts of fluids

- Extreme miniaturization:
 - Rapid and automated processes
 - Limited reagents consumption
 - Capillarity and surface interactions
- Multifunction integration
 - microfluidics + analytical techniques
 - replicate a real chemi/bio-lab on chip

Our approach

On-chip optical sensing by means of femtosecond laser written 3D photonic devices







Capillary electrophoresis in Lab on a Chip

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The flow of molecules is driven by voltages applied to the reservoirs



Molecules will separate in the channel according to the **different mobility**

They are **identified** on the basis of the **arrival time** at the detection point



Application: separation of DNA fragments to perform bioassays for the detection of a variety of diseases.

Exogenous DNA detection: viruses and bacteria.

Endogenous DNA mutation detection: cancer, hereditary genetic diseases





Confocal microscope for off-chip detection

Optical detection

- Fluorescence
- Absorbance
- Refractive index

Off-chip approach

External bulky equipment that needs precise alignment U Lab-on-chip miniaturization is frustrated

On-chip approach

Monolithic integration of photonic devices with one-time alignment Increased compactess and portability but increased fabrication complexity

Femtosecond laser post-processing of lab-on-chips





Post-processing on an already made Lab-on-a-chip.

- Fabrication of three-dimensional devices.
- High versatility and limited equipment costs.



 Commercial microfluidic chip for capillary electrophoresis (by LioniX bV)





> Inscribed optical waveguide allows selective excitation in the channel



Microchannel filled with rhodamine 6G Microscope image through a cut-off filter at 570 nm

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On-chip waveguide integration

Pigtailed excitation and collection fibers provide a very compact and portable unit



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On-chip Laser Induced Fluorescence detection 59



Limit of detection ~10 pM, among the best results for integrated detection

R. Martinez Vazquez et al., Lab Chip 9, 91 (2009)



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- CCD imaging of laser induced fluorescence by a fs-laser written waveguide
- Sample is a highly concentrated solution of two different dyes (Rhodamine 6G and Rhodamine B)



C. Dongre et al., Opt. Lett. 33, 2503-2505 (2008).

Dynamic Detection of labelled DNA fragments



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Monitoring chemical reactions in microreactors through interferometry in the **Mach-Zehnder** configuration

- Need for spatial resolution \Rightarrow
 - interferometer **orthogonal** to the separation channel
- Channel width of only L = 50 μ m \Rightarrow

evanescent field sensing too weak \Rightarrow

one arm of the interferometer is crossing the channel





Fringe shift

The phase shift acquired in the channel induces a fringe shift

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Mach-Zender integration



Microchannel shaping applications

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• Channel with top access holes (U-shape)



BEFORE etching



AFTER etching



• Fannel-shape channel (shape control along the channel axis)





AFTER etching



• O-groove for fiber coupling Waveguide 50 µm 1.5 mm



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Optical dual-beam trap for single cell (*1µm wavelength*):

- non-focusing counter-propagating beams can trap single cells
- increasing the optical power the trapped cell is stretched along the beam axis



standard configuration: cell suspension in between 2 counter-propagating *fibers*

- misalignement between discrete optical and fluidic components
- system suffers for vibrations and fluctuations





monolithic configuration: optical waveguides crossing the microfluidic channel with the flowing cell suspension in a *glass chip*

- no alignement + vibration problems
- higher system portability
- possibility of adding other waveguides for further optical funcionalities

Cooperation with University of Pavia

Optical stretcher: fabrication

• Microchannel fabrication with larger access holes for capillary connection



• "self-aligned" optical waveguides at different distance and depth with respect to the channel



Optical stretcher: experimental results

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Test the system on red blood cells (RBCs)





TRAPPING

balancing optical power at the two waveguides (P_{opt}≈20mW)

MOVING

unbalancing the power at the two waveguides

STRETCHING

simoultaneously increasing the power at the two waveguides (P_{opt}≈300mW)

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Femtosecond writing is a simple and powerful technique for the direct fabrication of high quality optical waveguides

 A variety of passive and active devices, both 2D and 3D, can be manufactured in various glass substrates

Femtosecond laser irradiation + etching provides directly buried 3D microchannels

 Waveguides and channels can be integrated in different geometries to implement optofluidic functionalities



Laser





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DACO 5° FP EU CRAFT-project



HIBISCUS 6th FP EU STREP-project www.fisi.polimi.it/hibiscus



microFLUID 7th FP EU STREP-project www.fisi.polimi.it/microfluid



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Photovoltaics (Si-based): state of the art

- Photovoltaic (PV) industry faces several challenges to achieve a competitive cost per kilowatt-hour for electricity over the life of the system :
- Cost-reduction of the solar cells or modules
- Enhancement of module efficiency

Thin-film technologies result in the lowest price-per-watt, but crystalline (wafer-based) solar cells exhibit the highest efficiency. Commercially available monocrystalline-silicon cells currently achieve 12% to 19% efficiency (far from the theoretical goal of 35%). Competing technologies: amorphous thin-film Si; cadmium telluride; copper indium germanium selenide; III/V triple junction cells; organic cells.

Losses are caused by light reflection, carrier recombination, ohmic losses, shadowing effects of the front contacts, and so forth.

New cell concepts are aimed at finding solutions to reduce these losses.


Front contact patterning of a typical solar cell can shadow up to 10% of the photoactive area. To reduce such effect contacts can be taken through the backside of the solar cell: e.g. MWT (metal wrap through) approach



For MWT 50 to 100 µm via holes must be drilled through 160-200 µm thick silicon wafers. Advantages: electrical connections to the cell and resistance (ohmic) losses are reduced because the dimensions of the contacts at the backside are no longer limited by shadowing effects. Around 100 holes per second to be drilled. Few 100-1500 ns laser pulses are sufficient for the drilling step, followed by post-processing (damage etching, silicon nitride coating, printing of electrical contacts. Efficiency increase in commercial cells 1%.

Are ns-laser pulses sufficient?

Nanosecond pulses may cause thermal effects during scribing that generate recombination centers in the bulk silicon. To reduce or prevent melting effects picosecond or femtosecond lasers can be used.

By using femtosecond laser pulses the shape of microscopic pyramidal structures is preserved even after scribing with the laser.



A micrograph shows c-Si surface structure after KOH etching. Single-shot femtosecond laser processing (round spots) preserves these structures without melting. (Courtesy of Jenoptik)



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Within the frame of classical cell structure with frontside and backside contacts, laser diffusion or laser doping is a hot topic in crystalline solar-cell manufacturing to enhance cell efficiency.



Selective emitter doping is a laser-based technique that can enhance PV cell efficiency by reduction of ohmic losses at the contacts. (Courtesy of Jenoptik)

Selective doping of the silicon allows reduction of the electrical resistance (ohmic losses) of the bulk silicon material underneath the contact fingers. Absolute cell efficiency increases by 0.3-0.5%. In this process a phosphorus coating diffuses from the surface into the bulk silicon at the locations where the silicon is melted by the laser (i.e. where the contact fingers are later located. The sheet resistance of laser-treated vs untreated area is strongly reduced, e.g. 120-150 ohm/sq to 20 ohm/sq. CW or ns-pulses high power lasers (hundreds of Watts) are required.



Texture is one of the critical surface parameters affecting solar-cell efficiency. A polished wafer of monocrystalline silicon (as in a bare semiconductor-grade silicon wafer) is about 40% reflective, depending on the wavelength of the incident radiation. A widely accepted technique to reduce this reflectivity is to texture (roughen) the surface so that reflected photons have a chance of being incident on

Surface Texture Differs Between Differently Efficient Cells



another facet of the PV cell. creating another opportunity for PV interaction in the emitter If the surface layer. roughness is too great, however, then the mean free path (MFP) of the electron/hole pair may elongate to the point where the probability of them recombining reduces the overall efficiency.



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Low resolution SEM of the black silicon surface High resolution SEM of the black silicon surface A. Serpengüzel et al., J. of Nanophotonics 2, 021770 (2008)

Black silicon samples are manufactured by shining very short (fs), very intense laser pulses at a silicon surface in air or sulfur-containing gas: air/gas reacts with the silicon surface and etches away some of it, leaving a spiked surface that is strongly light-absorbing: the surface of silicon, normally gray and shiny, turns deep black. Non-textured silicon absorbs a moderate amount of visible light, but with a substantial reflection, while IR and UV light are transmitted or reflected with very little absorption. Spiked silicon surfaces, in contrast, absorb nearly all light at wavelengths ranging from the ultraviolet to the infrared.

Micro and nano-structuring of Si by fs laser 77

- Halbwax et al (*Thin Solid Films 516 (2008) 6791-6795*) created a photovoltaic structure in a Si wafer by nanostructuring the surface with a fs laser before the formation of p-n junction. By optimizing the laser parameters (polarization, spot size, energy density, number of shots, scanning parameters) appropriate nanotexturization is achieved by laser treatment under vacuum (10^{-5} mbar), without SF₆.
- The p-n junction is obtained by counterdoping the wafer surface by means of plasma immersion technique followed by rapid thermal annealing.

The photocurrent increases by 25-30% in the texturized areas.

Processing steps of the photocell

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a) cleaning; b) creation of n⁺ layer by diffusion; c) removal of the front n⁺ layer;

d) fs laser structuring; e) plasma immersion doping; f) metallization of contact



The engraving of Si (001) was carried out in a vacuum system with a pressure of 5×10^{-5} to 1×10^{-5} mbar. Experiments were performed using a Ti:sapphire laser (800 nm, 500 µJ energy, 1 kHz repetition rate, 100 fs pulses). Two laser fluences were used: 140 and 185 mJ/cm². The laser-induced structuring of the sample surfaces was produced by scanning a straight line (30 µm width) at a speed-velocity of 150 µm/s, with different d shifts (1, 2, 5 and 15 µm) between the scans to treat the whole surface and study the overlap effect.



SEM photo of Laser Induced Periodic Surface Structures (LIPSS): original Si surface (left); capillary waves (periodicity 800 nm, center) and beads (about 2 µm, right). The latter are formed with higher number of pulses and energy density, since capillary waves tend to collapse and form hydrodynamically stable structures

Halbwax et al (2008)





SEM photo of penguin-like structures (height approx 10 μm, spacing 2.5 μm) created by femtosecond laser (top left corner is a picture of a real penguin colony in Antartica, photo by G. DARGAUD www.gdargaud.net).

Reflectivity of nanostructured surfaces



Left: 3D optical simulation of the optical absorption/reflectivity of a silicon surface with different texturizations: a) spikes b) "penguin-like" texturization c) pillars d) KOH pyramids e) flat; Right: real sample of a laser structured silicon (penguin-like).

Neflectivity of nanostructured surfaces

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Detail of the structures used for the 3D optical simulation: a) spikes (require SF₆ gas) b) "penguin-like" texturization c) pillars d) KOH pyramids e) flat.

Reflectivity of nanostructured surfaces

Structure	Height (µm)	FWHM diameter (µm)	Spacing (µm)	Reflectiv. <i>R</i> (%) visible	Absorption A (%) visible
Spikes (a)	10	2.5	4	6	94
Penguin- like (b)	10	2.5	4	9	91
Pillars (c)	10	1.5	2	21	79
Pyramids (d)	5	2.5	4	27	73
Flat (e)	-	-	-	35	65





LBIC scan maps showing the increase in the photocurrent in the laser treated zones. 30 µm spot size, v=150 µm/s, a) F=140 mJ/cm², d=1 µm b) F=140 mJ/cm², d=2 µm c) F=185 mJ/cm², d=1 µm d) F=185 mJ/cm², d=2 µm.





Optical microscope view (dark field) of a laser treated area (F=185 mJ/cm², v=150 µm/s) showing the nanoparticle redeposition outside the spot: increased absorption.



- Laser micro and nanostructured Si structures exhibit reduced reflection and high absorption (black silicon)
- Absorption increase also around the laser-treated area due to nanoparticle redeposition
- Photocurrent increase in the laser-treated areas
- Promising samples were obtained in void, with no use of SF₆, identified by the Kyoto Protocol as one of the main greenhouse gas that contribute to climate change and global warming